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(54) SEMICONDUCTOR DEVICE INCLUDING VERTICAL MOSFET AND METHOD OF MANUFACTURING THE SAME

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(57) **ABSTRACT**

A semiconductor device that achieves both miniaturization and high breakdown voltage is disclosed. The semiconductor device has a gate electrode G1 formed in a trench TR extending in Y direction and a plurality of column regions PC including column regions PC1 to PC3 formed in a drift region ND. The column regions PC1, PC2 and PC3 are provided in a staggered manner to sandwich the trench TR. An angle θ1 formed by a line connecting the centers of the column regions PC1 and PC2 and a line connecting the centers of the column regions PC1 and PC3 is 60 degrees or more and 90 degrees or less.